TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7MH4040FK

#### 12-Stage Ripple-Carry Binary Counter

The TC7MH4040FK is an advanced high speed CMOS 12-stage ripple-carry binary counter fabricated with silicon gate  ${\rm C^2MOS}$  technology.

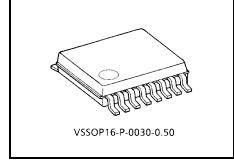
It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

Setting CLR to high resets the counter to low.

A negative transition on the  $\overline{CK}$  input brings one increment into the counter.

This counter provides all divided output stages, and at Q12, a 1/4096 divided frequency will be output.

An input protection circuit ensures that 0 to 5.5~V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5~V to 3~V systems and two



Weight: 0.02 g (typ.)

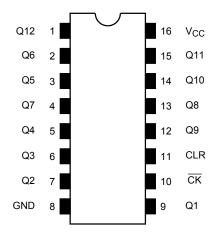
supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

#### **Features**

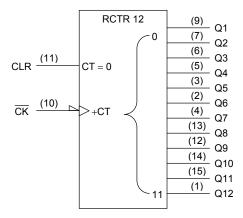
- High speed:  $f_{max} = 210 \text{ MHz (typ.)} \text{ (VCC} = 5 \text{ V)}$
- Low power dissipation:  $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- High noise immunity: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays:  $t_{pLH} \approx t_{pHL}$
- Wide operating voltage range:  $V_{CC (opr)} = 2 \sim 5.5 \text{ V}$
- Low noise:  $V_{OLP} = 1.5 \text{ V (max)}$
- Pin and function compatible with 74HC4040

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# Pin Assignment (top view)



# **IEC Logic Level**

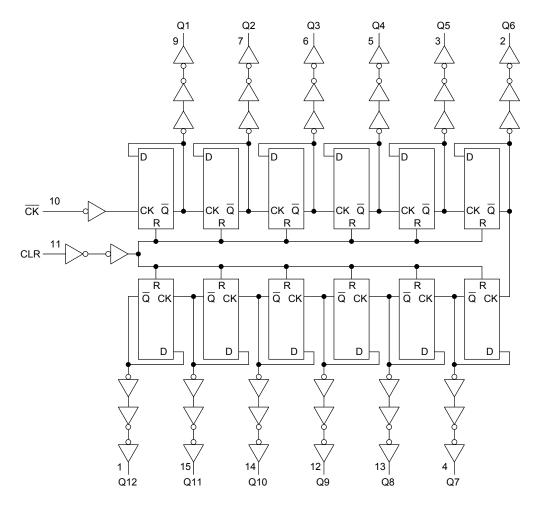


# **Truth Table**

CK	CLR	Outputs
Х	Н	All outputs = "L"
	L	No change
$\neg$	L	Advance to next state

X: Don't care

#### **System Diagram**



### **Absolute Maximum Ratings (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	VIN	-0.5~7.0	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	lıĸ	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±100	mA
Power dissipation	PD	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, may lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

# **Operating Ranges (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2.0~5.5	V
Input voltage	V <sub>IN</sub>	0~5.5	٧
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~100 (V <sub>CC</sub> = 3.3 ± 0.3 V)	ns/V
input noc and fail time	audv	$0\sim20 \ (V_{CC}=5\pm0.5 \ V)$	113/ V

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either  $V_{CC}$  or GND.

#### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics		Symbol	bol Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Cilaiat	- J		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic		
					2.0	1.50	_	_	1.50	_	
Input voltage	High level	VIH	_		3.0~5.5	V <sub>CC</sub> × 0.7	_	_	V <sub>CC</sub> × 0.7	_	V
input voitage					2.0		_	0.50	_	0.50	V
	Low level	V <sub>IL</sub>		_				V <sub>CC</sub> × 0.3	_	V <sub>CC</sub> × 0.3	
			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -50 \mu A$	2.0	1.9	2.0	_	1.9	_	
		Voн			3.0	2.9	3.0	_	2.9	_	
Output	High level				4.5	4.4	4.5	_	4.4	_	
				I <sub>OH</sub> = -4 mA	3.0	2.58	_	_	2.48	_	
				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	
voltage				$I_{OL} = 50 \mu A$	2.0	_	0	0.1	_	0.1	V
					3.0	_	0	0.1	_	0.1	
	Low level	$V_{OL}$	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		4.5	_	0	0.1	_	0.1	
			S. VIL	I <sub>OL</sub> = 4 mA	3.0	_	_	0.36	_	0.44	
				I <sub>OL</sub> = 8 mA	4.5	_	_	0.36	_	0.44	
Input leakage	current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0~5.5	_	_	±0.1	_	±1.0	μА
Quiescent sup	ply current	Icc	$V_{IN} = V_{CC}$ or GND		5.5	_	_	4.0	_	40.0	μΑ

# Timing Requirements (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	mbol Test Condition		Ta = 25°C		Ta = -40~85°C	Unit
	Syllibol	rest Condition	V <sub>CC</sub> (V)	Тур.	Limit	Limit	Offic
Minimum pulse width	tw (L)	_	$3.3 \pm 0.3$	_	5.0	5.0	ns
( <del>CK</del> )	t <sub>w (H)</sub>	_	$5.0\pm0.5$	_	5.0	5.0	115
Minimum pulse width	<b>t</b> 4.5		$3.3 \pm 0.3$	_	5.0	5.0	ns
(CLR)	t <sub>w (H)</sub>	_	$5.0\pm0.5$	_	5.0	5.0	115
Minimum removal time	t <sub>rem</sub>		$3.3 \pm 0.3$	_	5.0	5.0	ns
			$5.0\pm0.5$	_	5.0	5.0	115



# AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol Test Condition				Ta = 25°C			Ta = -40~85°C		Unit
Onal acteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Offic
			3.3 ± 0.3	15	_	7.5	11.9	1.0	14.0	ns
Propagation delay time	t <sub>pLH</sub>		0.0 ± 0.0	50	_	10.0	15.4	1.0	17.5	
( <del>CK</del> - Q1)	t <sub>pHL</sub>		5.0 ± 0.5	15		4.8	7.3	1.0	8.5	113
			5.0 ± 0.5	50		6.3	9.3	1.0	10.5	
Propagation delay time	At .	_	$3.3 \pm 0.3$	50		2.4	4.4	1.0	5.0	ns
$(Q_n - Q_n + 1)$	$\Delta t_{pd}$		$5.0 \pm 0.5$	50	_	1.6	3.1	1.0	3.5	115
	t <sub>pHL</sub>	_	3.3 ± 0.3	15	_	8.3	12.8	1.0	15.0	- ns
Propagation delay time				50	_	10.8	16.3	1.0	18.5	
(CLR - Q)			5.0 ± 0.5	15	_	5.6	8.6	1.0	10.0	
				50		7.1	10.6	1.0	12.0	
	ť		3.3 ± 0.3	15	75	140		75	_	
Maximum clock frequency			3.3 ± 0.3	50	55	80		50		MHz
waximum clock frequency	f <sub>max</sub>		5.0 ± 0.5	15	150	210	_	125		IVIITZ
			0.0 ± 0.0	50	95	125	_	80	—	
Input capacitance	C <sub>IN</sub>	-	_		_	4	10		10	pF
Power dissipation capacitance	C <sub>PD</sub>			(Note)	_	21	_	_	_	pF

Note: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

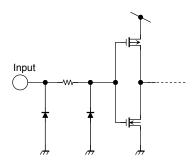
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

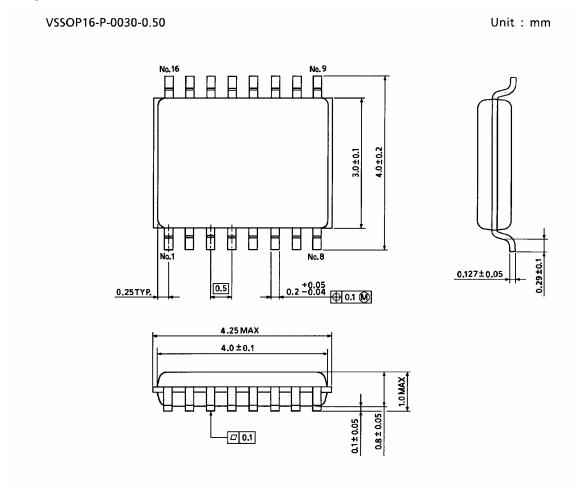
# Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics	Symbol	Test Condition		Ta =	25°C	Unit
Characteristics	Syllibol	rest condition	V <sub>CC</sub> (V)	Тур.	Limit	
Quiet output maximum dynamic V <sub>OL</sub>	V <sub>OLP</sub>	C <sub>L</sub> = 50 pF	5.0	1.2	1.5	V
Quiet output minimum dynamic V <sub>OL</sub>	V <sub>OLV</sub>	C <sub>L</sub> = 50 pF	5.0	-1.2	-1.5	V
Minimum high level dynamic input voltage $V_{\mbox{\scriptsize IH}}$	V <sub>IHD</sub>	C <sub>L</sub> = 50 pF	5.0	_	3.5	V
Minimum low level dynamic input voltage $V_{\text{IL}}$	V <sub>ILD</sub>	$C_L = 50 \text{ pF}$	5.0		1.5	V

# **Input Equivalent Circuit**



# **Package Dimensions**



Weight: 0.02 g (typ.)

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20070701-EN GENERAL

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